



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

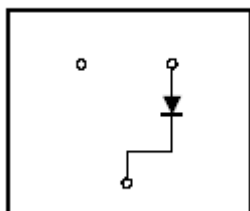
SOT-23-3L Plastic-Encapsulate Transistors

RB411D Schottky barrier Diodes

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

●Circuit



SOT-23-3L



Marking:D3E

Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	20	V
Mean rectifying current	I _O	500	mA
Peak forward surge current	I _{FSM}	3	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{F1}			0.3	V	I _F =10mA
	V _{F2}			0.5	V	I _F =500mA
Reverse current	I _R			30	μA	V _R =10V
Capacitance between terminals	C _T		20		pF	V _R =10V,f=1MHz

Typical Characteristics

RB411D

●Electrical characteristic curves (Ta = 25°C)

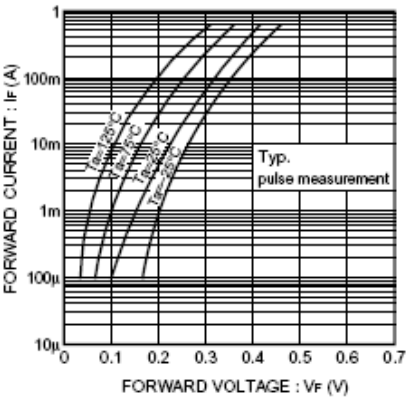


Fig. 1 Forward characteristics

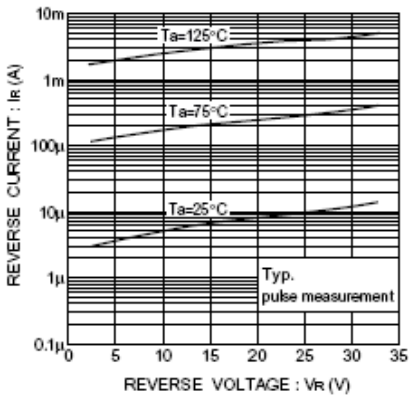


Fig. 2 Reverse characteristics

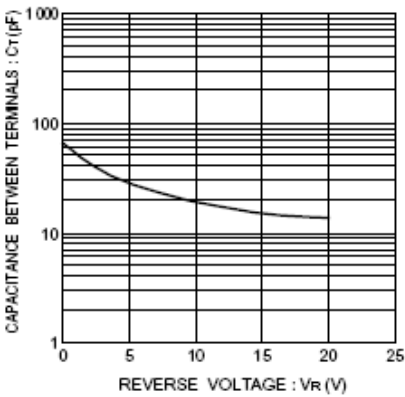


Fig. 3 Capacitance between terminals characteristic